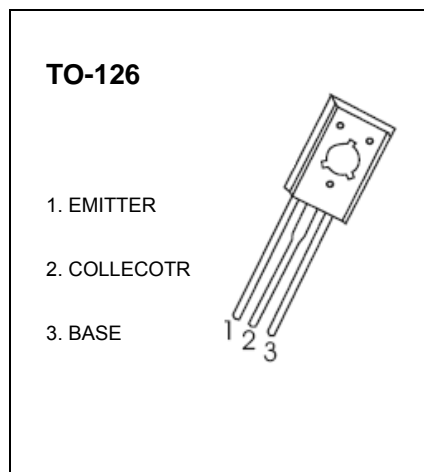


TO-18 Plastic-Encapsulate Transistors

2SC1162 TRANSISTOR (NPN)

FEATURES

- Low Frequency Power Amplifier



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CE0}	Collector-Emitter Voltage	35	V
V _{CEO}	Collector-Emitter Voltage	35	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	2.5	A
P _C	Collector Power Dissipation	1	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 1mA, I _E = 0	35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10mA, I _B = 0	35			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 1mA, I _C = 0	5			V
Collector cut-off current	I _{CBO}	V _{CB} = 35V, I _E = 0			20	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C = 0			20	μA
DC current gain	h _{FE1}	V _{CE} = 2V, I _C = 0.5A	60		320	
	h _{FE2}	V _{CE} = 2V, I _C = 1.5A*	20			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 2A, I _B = 200mA			1	V
Base-collector voltage	V _{BE}	V _{CE} = 2V, I _C = 1.5A			1.5	V
Transition frequency	f _T	V _{CE} = 2V, I _C = 200mA		180		MHz

* pulse test

CLASSIFICATION OF h_{FE1}

Rank	B	C	D
Range	60-120	100-200	160-320